Inventor: Demetrius Sarigiannis, Garo J. Derderian and Cem Basceri

Title: Methods of Forming Layers Over Substrates; and Methods

of Forming Trenched Isolation Regions

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is directed to the references listed on the attached Form PTO-1449 and copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Date: 6/26/2003 Attorney: Am

David G. Latwesen, Ph.D.

Reg. No. 38,533 Wells, St. John P.S. EV317136178

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| | 45 | WO 02070/2 42 | 04/04/02 | WIDO | | | | Yes | No | |
| | AF AG | WO 02/27063 A2 | 04/04/02 | WIPO | | | | | | |
| OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | | | | |
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